



## Tentative Program – Workshop

# WIDE BANDGAP SEMICONDUCTORS AND DEVICES

(as of 30/01/2024)

### MONDAY MARCH 18, 2024

08:30-09:15	<b>Registration</b>	
09:15-09:30	<b>Welcome</b>	
09:30-10:10	<b>Fabrizio Roccaforte</b> (CNR-IMM, Italy) Novel Trends in Interface Engineering for Wide Band Gap (SiC and GaN) power devices	
10:10-11:10		<b>Coffee Break</b>
11:10-11:50	<b>Ferdinando Iucolano</b> (STMicroelectronics, Italy) GaN devices: Industrial trends and challenges	
11:50-12:30	<b>Mario Saggio</b> (STMicroelectronics, Italy) Silicon Carbide technologies for high demanding power applications	
12:30-13:45		<b>Lunch</b>
13:45-14:25	<b>Daniel Alquier</b> (Université de Tours, France) Contact Strategies for SiC Power Devices	
14:25-15:05	<b>Alessandro Chini</b> (University of Modena and Reggio Emilia, Italy) Characterization and Modelling of C-doped buffers in GaN HEMTs	
15:05-15:25		<b>Coffee Break</b>
15:25-16:05	<b>Farid Medjoub</b> (I.E.M.N – CNRS, France) Local substrate removal enabling next generation fully vertical GaN-on-Si power devices	
16:05-16:45	<b>Johannes Heitmann</b> (Freiberg University, Germany) Ohmic Contact Formation and Atomic Layer Processing for Nitride Devices	